

Czeslaw Skierbiszewski

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#	Paper	IF	Citations
222	Weak antilocalization and spin precession in quantum wells. <i>Physical Review B</i> , 1996 , 53, 3912-3924	3.3	358
221	Large, nitrogen-induced increase of the electron effective mass in InyGa1-yNxAs1-x. <i>Applied Physics Letters</i> , 2000 , 76, 2409-2411	3.4	212
220	AlGaIn/GaN high electron mobility transistors as a voltage-tunable room temperature terahertz sources. <i>Journal of Applied Physics</i> , 2010 , 107, 024504	2.5	103
219	High electron mobility in AlGaIn/GaN heterostructures grown on bulk GaN substrates. <i>Applied Physics Letters</i> , 2000 , 77, 2551-2553	3.4	103
218	Negative differential resistance in dislocation-free GaN/AlGaIn double-barrier diodes grown on bulk GaN. <i>Applied Physics Letters</i> , 2006 , 88, 172106	3.4	90
217	Experimental studies of the conduction-band structure of GaInNAs alloys. <i>Semiconductor Science and Technology</i> , 2002 , 17, 803-814	1.8	73
216	Cyclotron resonance and quantum Hall effect studies of the two-dimensional electron gas confined at the GaN/AlGaIn interface. <i>Applied Physics Letters</i> , 1997 , 70, 2123-2125	3.4	72
215	Blue-violet InGaIn laser diodes grown on bulk GaN substrates by plasma-assisted molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2005 , 86, 011114	3.4	62
214	Interband optical absorption in free standing layer of Ga0.96In0.04As0.99N0.01. <i>Applied Physics Letters</i> , 2000 , 76, 1279-1281	3.4	62
213	Band structure and optical properties of InyGa1-yAs1-xNx alloys. <i>Physical Review B</i> , 2001 , 65,	3.3	58
212	Effect of Nitrogen-Induced Modification of the Conduction Band Structure on Electron Transport in GaAsN Alloys. <i>Physica Status Solidi (B): Basic Research</i> , 1999 , 216, 135-139	1.3	56
211	High mobility two-dimensional electron gas in AlGaIn/GaN heterostructures grown on bulk GaN by plasma assisted molecular beam epitaxy. <i>Applied Physics Letters</i> , 2005 , 86, 102106	3.4	52
210	Evidence for localized Si-donor state and its metastable properties in AlGaIn. <i>Applied Physics Letters</i> , 1999 , 74, 3833-3835	3.4	50
209	Acoustic phonon scattering of two-dimensional electrons in GaN/AlGaIn heterostructures. <i>Applied Physics Letters</i> , 2002 , 80, 1228-1230	3.4	46
208	60mW continuous-wave operation of InGaIn laser diodes made by plasma-assisted molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2006 , 88, 221108	3.4	45
207	Nitride-based laser diodes by plasma-assisted MBE from violet to green emission. <i>Journal of Crystal Growth</i> , 2009 , 311, 1632-1639	1.6	43
206	Nitride-based laser diodes grown by plasma-assisted molecular beam epitaxy. <i>Journal Physics D: Applied Physics</i> , 2014 , 47, 073001	3	39

205	Optically pumped 500 nm InGaN green lasers grown by plasma-assisted molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2011 , 110, 063110	2.5	39
204	Growth optimisation of the GaN layers and GaN/AlGaIn heterojunctions on bulk GaN substrates using plasma-assisted molecular beam epitaxy. <i>Physica Status Solidi A</i> , 2004 , 201, 320-323		35
203	Nonequivalent atomic step edges Role of gallium and nitrogen atoms in the growth of InGaN layers. <i>Journal of Crystal Growth</i> , 2013 , 367, 115-121	1.6	34
202	Effective g^* factor of two-dimensional electrons in GaN/AlGaIn heterojunctions. <i>Applied Physics Letters</i> , 1999 , 75, 3156-3158	3.4	34
201	True-blue laser diodes with tunnel junctions grown monolithically by plasma-assisted molecular beam epitaxy. <i>Applied Physics Express</i> , 2018 , 11, 034103	2.4	34
200	Growth of InGaN and InGaN/InGaIn quantum wells by plasma-assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2008 , 310, 3983-3986	1.6	32
199	High power blue-violet InGaN laser diodes grown on bulk GaN substrates by plasma-assisted molecular beam epitaxy. <i>Semiconductor Science and Technology</i> , 2005 , 20, 809-813	1.8	30
198	Contactless electroreflectance studies of Fermi level position on c-plane GaN surface grown by molecular beam epitaxy and metalorganic vapor phase epitaxy. <i>Applied Physics Letters</i> , 2012 , 100, 181603	3.4	29
197	InGaN light emitting diodes for 415 nm-20 nm spectral range by plasma assisted MBE. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2009 , 6, S917-S920		29
196	Complete in-plane polarization anisotropy of the A exciton in unstrained A-plane GaN films. <i>Applied Physics Letters</i> , 2007 , 91, 141903	3.4	29
195	The surface boundary conditions in GaN/AlGaIn/GaN transistor heterostructures. <i>Applied Physics Letters</i> , 2011 , 98, 231902	3.4	27
194	Contactless electroreflectance of InGaN layers with indium content $\leq 6\%$: The surface band bending, band gap bowing, and Stokes shift issues. <i>Journal of Applied Physics</i> , 2009 , 106, 113517	2.5	26
193	Free and bound excitons in GaN/AlGaIn homoepitaxial quantum wells grown on bulk GaN substrate along the nonpolar (112 $\bar{0}$) direction. <i>Applied Physics Letters</i> , 2005 , 86, 162112	3.4	25
192	Growth of thin AlInGaInN quantum wells for applications to high-speed intersubband devices at telecommunication wavelengths. <i>Journal of Vacuum Science & Technology B</i> , 2006 , 24, 1505		24
191	Enhancement of optical confinement factor by InGaN waveguide in blue laser diodes grown by plasma-assisted molecular beam epitaxy. <i>Applied Physics Express</i> , 2015 , 8, 032103	2.4	23
190	Growth mechanism of InGaN by plasma assisted molecular beam epitaxy. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2011 , 29, 03C136	1.3	23
189	Stack of two III-nitride laser diodes interconnected by a tunnel junction. <i>Optics Express</i> , 2019 , 27, 5784-5791		22
188	Elimination of leakage of optical modes to GaN substrate in nitride laser diodes using a thick InGaN waveguide. <i>Applied Physics Express</i> , 2016 , 9, 092103	2.4	21

187	Control of Mg doping of GaN in RF-plasma molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2005 , 278, 443-448	1.6	21
186	Pressure and composition dependence of the electronic structure of GaAs _{1-x} N _x . <i>Physical Review B</i> , 2002 , 66,	3.3	21
185	The influence of hydrostatic pressure on the formation of a donor superlattice in HgSe:Fe. <i>Semiconductor Science and Technology</i> , 1989 , 4, 293-295	1.8	21
184	Growth mechanisms in semipolar and nonpolar m-plane AlGaIn/GaN structures grown by PAMBE under N-rich conditions. <i>Journal of Crystal Growth</i> , 2013 , 377, 184-191	1.6	20
183	The electron effective mass at the bottom of the GaNAs conduction band. <i>Semiconductor Science and Technology</i> , 2004 , 19, 1189-1195	1.8	19
182	Spin and interaction effects in Shubnikov-de Haas oscillations and the quantum Hall effect in GaN/AlGaIn heterostructures. <i>Journal of Physics Condensed Matter</i> , 2004 , 16, 3421-3432	1.8	19
181	Hydrogen diffusion in GaN:Mg and GaN:Si. <i>Journal of Alloys and Compounds</i> , 2018 , 747, 354-358	5.7	18
180	Role of dislocation-free GaN substrates in the growth of indium containing optoelectronic structures by plasma-assisted MBE. <i>Journal of Crystal Growth</i> , 2007 , 305, 346-354	1.6	18
179	Effective mass and conduction band dispersion of GaAsN/GaAs quantum wells. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002 , 13, 1078-1081	3	18
178	Contactless electroreflectance studies of surface potential barrier for N- and Ga-face epilayers grown by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2013 , 103, 052107	3.4	17
177	Step-flow anisotropy of the m-plane GaN (11 $\bar{0}$ 0) grown under nitrogen-rich conditions by plasma-assisted molecular beam epitaxy. <i>Physical Review B</i> , 2011 , 83,	3.3	17
176	The light-hole mass in a strained InGaAs/GaAs single quantum well and its pressure dependence. <i>Journal of Physics and Chemistry of Solids</i> , 1995 , 56, 469-473	3.9	17
175	Beyond Quantum Efficiency Limitations Originating from the Piezoelectric Polarization in Light-Emitting Devices. <i>ACS Photonics</i> , 2019 , 6, 1963-1971	6.3	16
174	True-Blue Nitride Laser Diodes Grown by Plasma-Assisted Molecular Beam Epitaxy. <i>Applied Physics Express</i> , 2012 , 5, 112103	2.4	16
173	Blue Laser on High N ₂ Pressure-Grown Bulk GaN. <i>Acta Physica Polonica A</i> , 2001 , 100, 229-232	0.6	16
172	Indium incorporation in semipolar (202 1) and nonpolar (101 0) InGaIn grown by plasma assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2017 , 459, 129-134	1.6	15
171	AlGaIn-Free Laser Diodes by Plasma-Assisted Molecular Beam Epitaxy. <i>Applied Physics Express</i> , 2012 , 5, 022104	2.4	15
170	InGaIn laser diodes operating at 450-60 nm grown by rf-plasma MBEa). <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2012 , 30, 02B102	1.3	15

169	Terahertz 3D printed diffractive lens matrices for field-effect transistor detector focal plane arrays. <i>Optics Express</i> , 2016 , 24, 20119-31	3.3	15
168	Surface and in-depth characterization of InGaN compounds synthesized by plasma-assisted molecular beam epitaxy. <i>Journal of Alloys and Compounds</i> , 2011 , 509, 9565-9571	5.7	14
167	Optically pumped GaN/AlGaIn separate-confinement heterostructure laser grown along the (112̄0) nonpolar direction. <i>Applied Physics Letters</i> , 2007 , 90, 081104	3.4	14
166	Bulk GaN crystals grown at high pressure as substrates for blue-laser technology. <i>Physica Status Solidi A</i> , 2003 , 200, 9-12		14
165	High power nitride laser diodes grown by plasma assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2015 , 425, 398-400	1.6	13
164	MBE fabrication of III-N-based laser diodes and its development to industrial system. <i>Journal of Crystal Growth</i> , 2013 , 378, 278-282	1.6	13
163	Energy difference between electron subbands in AlInN/GaN quantum wells studied by contactless electroreflectance spectroscopy. <i>Applied Physics Letters</i> , 2006 , 89, 251908	3.4	13
162	Investigation of interface abruptness and In content in (In,Ga)N/GaN superlattices. <i>Journal of Applied Physics</i> , 2016 , 120, 125307	2.5	13
161	Unusual step meandering due to Ehrlich-Schwoebel barrier in GaN epitaxy on the N-polar surface. <i>Applied Surface Science</i> , 2019 , 484, 771-780	6.7	12
160	Determination of gain in AlGaIn cladding free nitride laser diodes. <i>Applied Physics Letters</i> , 2013 , 103, 061102	3.4	12
159	Step-flow growth mode instability of N-polar GaN under N-excess. <i>Applied Physics Letters</i> , 2013 , 103, 071601	3.4	12
158	Ultraviolet laser diodes grown on semipolar (202̄1) GaN substrates by plasma-assisted molecular beam epitaxy. <i>Applied Physics Letters</i> , 2013 , 102, 251101	3.4	12
157	Mismatch relaxation by stacking fault formation of AlN islands in AlGaIn/GaN structures on m-plane GaN substrates. <i>Applied Physics Letters</i> , 2011 , 99, 061901	3.4	12
156	Plasmon-cyclotron resonance in two-dimensional electron gas confined at the GaN/Al _x Ga _{1-x} N interface. <i>Physical Review B</i> , 2007 , 76,	3.3	12
155	Mode dynamics of high power (InAl)GaIn based laser diodes grown on bulk GaN substrate. <i>Journal of Applied Physics</i> , 2007 , 101, 083109	2.5	12
154	High temperature electrical investigations of (Al,Ga)N/GaN heterostructures [Hall sensor applications. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 1438-1443		12
153	Enhanced injection efficiency and light output in bottom tunnel-junction light-emitting diodes. <i>Optics Express</i> , 2020 , 28, 4489-4500	3.3	12
152	Investigation on the origin of luminescence quenching in N-polar (In,Ga)N multiple quantum wells. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013 , 31, 03C130	1.3	11

151	Effective g^* factor in the diluted nitrides $\text{Ga}_{1-x}\text{In}_x\text{N}_x\text{As}_{1-x}$. <i>Physical Review B</i> , 2005 , 71,	3.3	11
150	Comparison of the Luminous Efficiencies of Ga- and N-Polar $\text{In}_x\text{Ga}_{1-x}\text{N}/\text{In}_y\text{Ga}_{1-y}\text{N}$ Quantum Wells Grown by Plasma-Assisted Molecular Beam Epitaxy. <i>Physical Review Applied</i> , 2016 , 6,	4.3	11
149	Surface properties of c-plane GaN grown by plasma-assisted molecular beam epitaxy. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2013 , 31, 03C112	1.3	10
148	Transparency of Semi-Insulating, n-Type, and p-Type Ammonothermal GaN Substrates in the Near-Infrared, Mid-Infrared, and THz Spectral Range. <i>Crystals</i> , 2017 , 7, 187	2.3	9
147	Dependence of indium content in monolayer-thick $\text{InGa}_{1-x}\text{N}/\text{In}_{0.02}\text{Ga}_{0.98}\text{N}$ superlattices. <i>Journal of Applied Physics</i> , 2018 , 124, 065701	2.5	9
146	Separating strain from composition in unit cell parameter maps obtained from aberration corrected high resolution transmission electron microscopy imaging. <i>Journal of Applied Physics</i> , 2014 , 115, 033113	2.5	9
145	Ultraviolet light-emitting diodes grown by plasma-assisted molecular beam epitaxy on semipolar GaN (202°) substrates. <i>Applied Physics Letters</i> , 2013 , 102, 111107	3.4	9
144	High quality m-plane GaN grown under nitrogen-rich conditions by plasma assisted molecular beam epitaxy. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2011 , 29, 03C135	1.3	9
143	Low dislocation density, high power InGaN laser diodes. <i>MRS Internet Journal of Nitride Semiconductor Research</i> , 2004 , 9, 1		9
142	Determination of the basic parameters of pseudomorphic GaInAs quantum wells by means of simultaneous transport and optical investigations. <i>Solid-State Electronics</i> , 1994 , 37, 665-667	1.7	9
141	MBE grown GaN/AlGaIn lateral Schottky barrier diodes for high frequency applications. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016 , 34, 02L118	1.3	9
140	Extremely long lifetime of III-nitride laser diodes grown by plasma assisted molecular beam epitaxy. <i>Materials Science in Semiconductor Processing</i> , 2019 , 91, 387-391	4.3	9
139	Miscut dependent surface evolution in the process of N-polar. <i>Journal of Crystal Growth</i> , 2017 , 457, 38-456		8
138	Vertical Integration of Nitride Laser Diodes and Light Emitting Diodes by Tunnel Junctions. <i>Electronics (Switzerland)</i> , 2020 , 9, 1481	2.6	8
137	Luminescent N-polar $(\text{In,Ga})\text{N}/\text{GaN}$ quantum wells achieved by plasma-assisted molecular beam epitaxy at temperatures exceeding 700 °C. <i>Applied Physics Letters</i> , 2018 , 112, 022102	3.4	8
136	Influence of the growth method on degradation of InGaIn laser diodes. <i>Applied Physics Express</i> , 2017 , 10, 091001	2.4	8
135	Theoretical and experimental studies of electric field distribution in N-polar $\text{GaN}/\text{AlGaIn}/\text{GaN}$ heterostructures. <i>Applied Physics Letters</i> , 2015 , 107, 262107	3.4	8
134	Cyan laser diode grown by plasma-assisted molecular beam epitaxy. <i>Applied Physics Letters</i> , 2014 , 104, 023503	3.4	8

133	Electron spin resonance and Rashba field in GaN-based materials. <i>Physica B: Condensed Matter</i> , 2011 , 406, 2548-2554	2.8	8
132	Pressure Studies of Defects and Impurities in Nitrides. <i>Physica Status Solidi (B): Basic Research</i> , 1999 , 216, 521-528	1.3	8
131	Concentration dependent mobility of two-dimensional electron gas in GaAs/AlGaAs heterostructure. <i>Semiconductor Science and Technology</i> , 1991 , 6, 461-464	1.8	8
130	Switching of exciton character in double InGaN/GaN quantum wells. <i>Physical Review B</i> , 2018 , 98,	3.3	8
129	Optical properties of III-nitride laser diodes with wide InGaN quantum wells. <i>Applied Physics Express</i> , 2019 , 12, 072003	2.4	7
128	AlGa _x N/GaN HEMT's photoresponse to high intensity THz radiation. <i>Opto-electronics Review</i> , 2015 , 23,	2.4	7
127	Bandgap behavior of InGaN/GaN short period superlattices grown by metal-organic vapor phase epitaxy. <i>Physica Status Solidi (B): Basic Research</i> , 2017 , 254, 1600710	1.3	7
126	Two-dimensional electron gas mobility anomalies (and enhancement) in pseudomorphic AlGaAs/InGaAs/GaAs heterostructures. <i>Journal of Applied Physics</i> , 1995 , 77, 405-407	2.5	7
125	Elimination of DX centerlike behavior of donors in heavily doped GaAs. <i>Journal of Applied Physics</i> , 1991 , 69, 3087-3093	2.5	7
124	Waveguide Design for Long Wavelength InGaN Based Laser Diodes. <i>Acta Physica Polonica A</i> , 2012 , 122, 1031-1033	0.6	7
123	HVPE-GaN growth on GaN-based Advanced Substrates by Smart Cut. <i>Journal of Crystal Growth</i> , 2016 , 456, 73-79	1.6	7
122	Quantum-confined Stark effect and mechanisms of its screening in InGaN/GaN light-emitting diodes with a tunnel junction. <i>Optics Express</i> , 2021 , 29, 1824-1837	3.3	7
121	Sensitivity of Fermi level position at Ga-polar, N-polar, and nonpolar-m-plane GaN surfaces to vacuum and air ambient. <i>Japanese Journal of Applied Physics</i> , 2016 , 55, 05FA08	1.4	6
120	Influence of quantum well inhomogeneities on absorption, spontaneous emission, photoluminescence decay time, and lasing in polar InGaN quantum wells emitting in the blue-green spectral region. <i>Applied Physics A: Materials Science and Processing</i> , 2014 , 115, 1015-1023	2.6	6
119	Role of band potential roughness on the luminescence properties of InGaN quantum wells grown by MBE on bulk GaN substrates. <i>Physica Status Solidi (B): Basic Research</i> , 2006 , 243, 1614-1618	1.3	6
118	Zeeman splitting in GaInNAs. <i>Journal of Physics Condensed Matter</i> , 2004 , 16, S3319-S3331	1.8	6
117	Influence of dislocation and ionized impurity scattering on the electron mobility in GaN/AlGa _x N heterostructures. <i>Journal of Crystal Growth</i> , 2005 , 281, 194-201	1.6	6
116	Factors Governing the Photoluminescence Yield of Erbium Implanted Silicon. <i>Materials Research Society Symposia Proceedings</i> , 1996 , 422, 101		6

115	Metastable and nonmetastable deep states of Ge in GaAs. <i>Applied Physics Letters</i> , 1993 , 63, 3209-3211	3.4	6
114	Unusual Behaviour of the DX-Centre in GaAs:Ge. <i>Japanese Journal of Applied Physics</i> , 1993 , 32, 218	1.4	6
113	From High Electron Mobility GaN/AlGaN Heterostructures to Blue-Violet InGaN Laser Diodes. Perspectives of MBE for Nitride Optoelectronics. <i>Acta Physica Polonica A</i> , 2005 , 108, 635-651	0.6	6
112	Tunnel Junctions with a Doped (In,Ga)N Quantum Well for Vertical Integration of III-Nitride Optoelectronic Devices. <i>Physical Review Applied</i> , 2021 , 15,	4.3	6
111	Growth rate independence of Mg doping in GaN grown by plasma-assisted MBE. <i>Journal of Crystal Growth</i> , 2018 , 482, 56-60	1.6	6
110	Comparative study of semipolar(202 $\bar{1}$), nonpolar(10 $\bar{1}$ 0)and polar(0001)InGaN multi-quantum well structures grown under N- and In-excess by plasma assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2017 , 465, 43-47	1.6	5
109	Aluminum-free nitride laser diodes: waveguiding, electrical and degradation properties. <i>Optics Express</i> , 2017 , 25, 33113	3.3	5
108	Doping-Induced Contrast in the Refractive Index for GaInN/GaN Structures at Telecommunication Wavelengths. <i>Applied Physics Express</i> , 2009 , 2, 111001	2.4	5
107	Why various types of donor can either enhance or reduce electron mobility in narrow-gap semiconductors. <i>Semiconductor Science and Technology</i> , 1993 , 8, S40-S43	1.8	5
106	Unusual behaviour of the Ge DX centre in GaAs: coexistence of two localized donor states. <i>Journal of Physics Condensed Matter</i> , 1993 , 5, 5001-5008	1.8	5
105	Nitride LEDs and Lasers with Buried Tunnel Junctions. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 015018	2	5
104	Strain relaxation in semipolar (202 $\bar{1}$) InGaN grown by plasma assisted molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2016 , 119, 185701	2.5	5
103	Low frequency noise in two-dimensional lateral GaN/AlGaN Schottky diodes. <i>Applied Physics Letters</i> , 2016 , 109, 033502	3.4	5
102	Sensitivity of N-polar GaN surface barrier to ambient gases. <i>Sensors and Actuators B: Chemical</i> , 2019 , 281, 561-567	8.5	5
101	Nitrogen-rich growth for device quality N-polar InGaN/GaN quantum wells by plasma-assisted MBE. <i>Journal of Crystal Growth</i> , 2019 , 512, 208-212	1.6	4
100	Revealing inhomogeneous Si incorporation into GaN at the nanometer scale by electrochemical etching. <i>Nanoscale</i> , 2020 , 12, 6137-6143	7.7	4
99	Role of Nonequivalent Atomic Step Edges in the Growth of InGaN by Plasma-Assisted Molecular Beam Epitaxy. <i>Japanese Journal of Applied Physics</i> , 2013 , 52, 08JE02	1.4	4
98	Photo- and Electroluminescence of Erbium-Doped Silicon. <i>Materials Science Forum</i> , 1997 , 258-263, 1509-1514	0.5	4

97	Observation of quantum Hall effect in 2D-electron gas confined in GaN/GaN heterostructure. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1997 , 46, 92-95	3.1	4
96	Conduction Band Energy Spectrum of Two-Dimensional Electrons in GaN/AlGaN Heterojunctions. <i>Physica Status Solidi (B): Basic Research</i> , 1999 , 216, 719-725	1.3	4
95	Influence of Electric Field on Recombination Dynamics of Quantum Confined Carriers. <i>Acta Physica Polonica A</i> , 2007 , 112, 243-247	0.6	4
94	Stacking faults in plastically relaxed InGaN epilayers. <i>Semiconductor Science and Technology</i> , 2020 , 35, 034003	1.8	3
93	Impact of the substrate lattice constant on the emission properties of InGaN/GaN short-period superlattices grown by plasma assisted MBE. <i>Superlattices and Microstructures</i> , 2019 , 133, 106209	2.8	3
92	Theoretical simulations of radiative recombination time in polar InGaN quantum wells. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 2273-2275		3
91	Broadening of interband transitions in InGaN quantum wells. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2011 , 8, 2282-2284		3
90	Contactless electroreflectance of GaInN/AlInN multi quantum wells: The issue of broadening of optical transitions. <i>Microelectronics Journal</i> , 2009 , 40, 392-395	1.8	3
89	Properties of the Two-Dimensional Electron Gas Confined in GaN/AlGaN Interface Studied by Electron Spin Resonance. <i>AIP Conference Proceedings</i> , 2007 ,	0	3
88	Contactless electroreflectance spectroscopy of inter- and intersub-band transitions in AlInN/GaN quantum wells. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2008 , 5, 503-507		3
87	Comparison of gain in group-III-nitride laser structures grown by metalorganic vapour phase epitaxy and plasma-assisted molecular beam epitaxy on bulk GaN substrates. <i>Semiconductor Science and Technology</i> , 2007 , 22, 736-741	1.8	3
86	Growth and characterization of AlInN/GaN quantum wells for high-speed intersubband devices at telecommunication wavelengths 2006 ,		3
85	Far infrared spectroscopy with high resolution cyclotron resonance filters. <i>Journal of Applied Physics</i> , 1998 , 84, 433-438	2.5	3
84	The band structure of mixed-crystal Hg _{1-x} Fe _x Se. <i>Semiconductor Science and Technology</i> , 1993 , 8, S22-S25.8		3
83	Magnetotransport in high mobility InSb/CdTe heterojunctions: Electric spin-splitting of subbands and high pressure effects. <i>Superlattices and Microstructures</i> , 1991 , 9, 51-54	2.8	3
82	Crack Free GaInN/AlInN Multiple Quantum Wells Grown on GaN with Strong Intersubband Absorption at 1.55 μ m. <i>Acta Physica Polonica A</i> , 2006 , 110, 175-181	0.6	3
81	Enhancement of Intersubband Absorption in GaInN/AlInN Quantum Wells. <i>Acta Physica Polonica A</i> , 2008 , 114, 1093-1099	0.6	3
80	Far-Infrared Narrow-Band Photodetector Based on Magnetically Tunable Cyclotron Resonance-Assisted Transitions in Pure n-Type InSb. <i>Acta Physica Polonica A</i> , 1997 , 92, 733-736	0.6	3

79	Anomalous photocurrent in wide InGaN quantum wells. <i>Optics Express</i> , 2020 , 28, 4717-4725	3.3	3
78	Distributed-feedback blue laser diode utilizing a tunnel junction grown by plasma-assisted molecular beam epitaxy. <i>Optics Express</i> , 2020 , 28, 35321-35329	3.3	3
77	Nitride light-emitting diodes for cryogenic temperatures. <i>Optics Express</i> , 2020 , 28, 30299-30308	3.3	3
76	Hydrostatic pressure dependence of indirect and direct excitons in InGaN/GaN quantum wells. <i>Physical Review B</i> , 2020 , 101,	3.3	2
75	Lateral Schottky barrier diodes based on GaN/AlGaIn 2DEG for sub-THz detection 2016 ,		2
74	Surface potential barrier in-plane GaN studied by contactless electroreflectance. <i>Applied Physics Express</i> , 2016 , 9, 021002	2.4	2
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